

**Features**

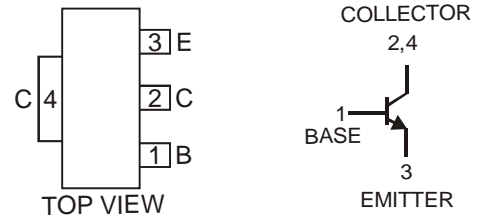
- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Resistance  $R_{CE(SAT)} = 75m\Omega$  at 4A
- Complementary PNP Type Available (2DB1386)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT89-3L

**Mechanical Data**

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



Schematic and Pin Configuration

**Maximum Ratings** @  $T_A = 25^\circ C$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	20	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Peak Pulse Current	$I_{CM}$	10	A
Continuous Collector Current	$I_C$	5	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ C$	$P_D$	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ C$	$R_{\theta JA}$	125	$^\circ C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

**Electrical Characteristics** @  $T_A = 25^\circ C$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Conditions
<b>OFF CHARACTERISTICS (Note 4)</b>						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50	—	—	V	$I_C = 50\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1mA, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 50\mu A, I_C = 0$
Collector Cut-Off Current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB} = 40V, I_E = 0$
Emitter Cut-Off Current	$I_{EBO}$	—	—	0.5	$\mu A$	$V_{EB} = 5V, I_C = 0$
<b>ON CHARACTERISTICS (Note 4)</b>						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.3	1.0	V	$I_C = 4A, I_B = 0.1A$
DC Current Gain	$h_{FE}$	180	—	390	—	$I_C = 0.5A, V_{CE} = 2V$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Transition Frequency	$f_T$	—	220	—	MHz	$V_{CE} = 6V, I_E = -50mA, f = 100MHz$
Output Capacitance	$C_{ob}$	—	14	—	pF	$V_{CB} = 20V, I_E = 0, f = 1MHz$

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  4. Measured under pulsed conditions. Pulse width = 300 $\mu s$ . Duty cycle  $\leq 2\%$ .

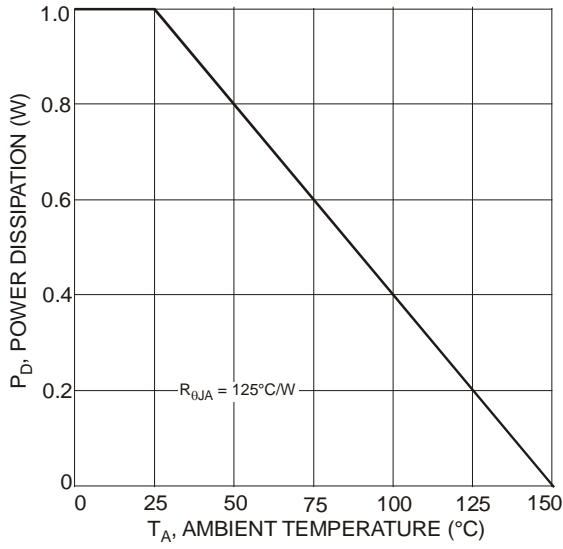


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

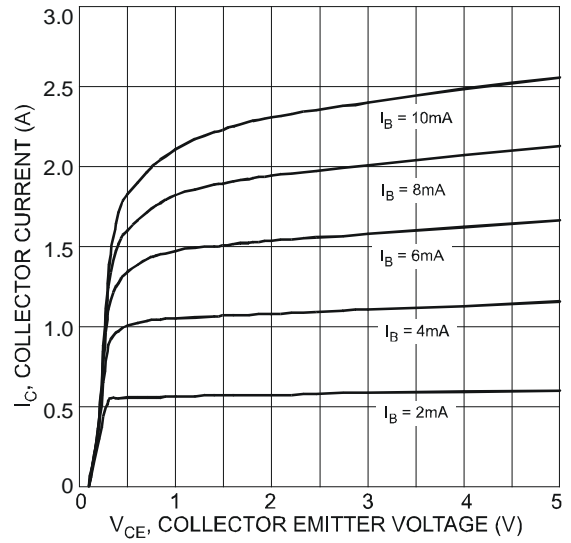


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

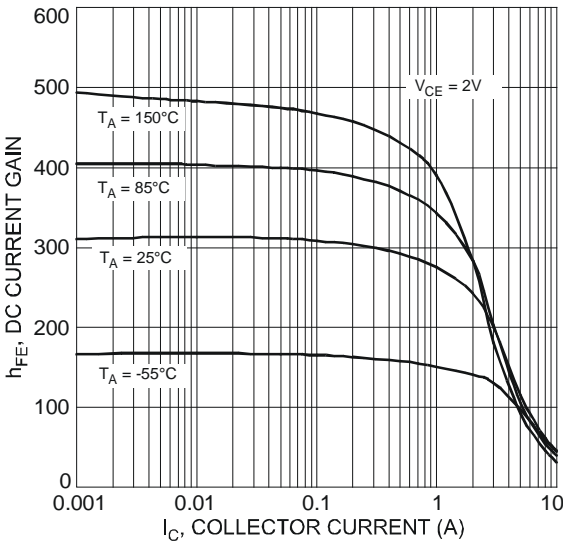


Fig. 3 Typical DC Current Gain vs. Collector Current

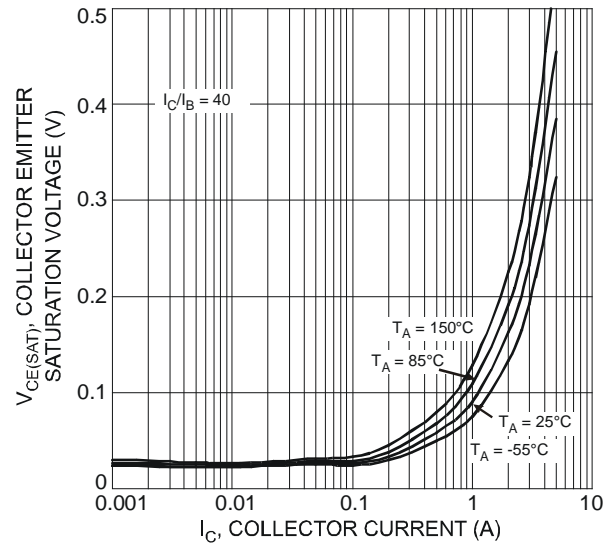


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

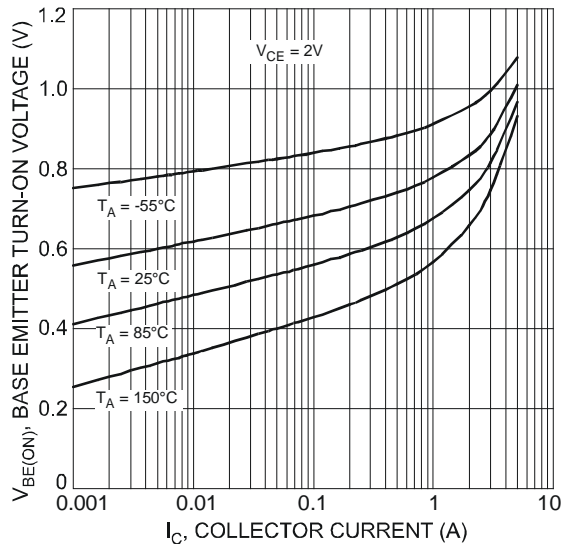


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

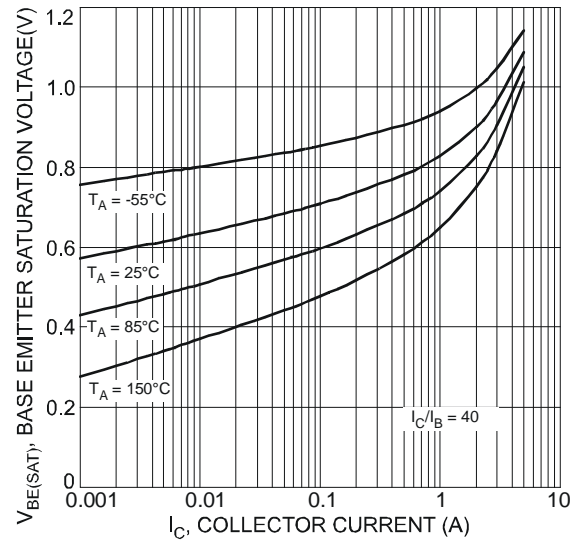


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

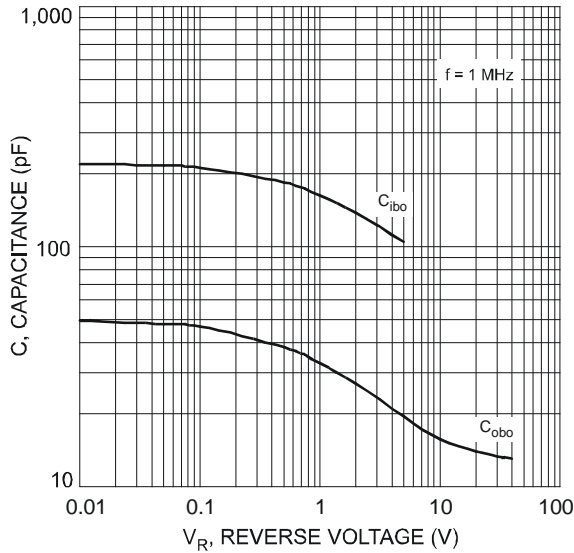


Fig. 7 Typical Junction Capacitance Characteristics

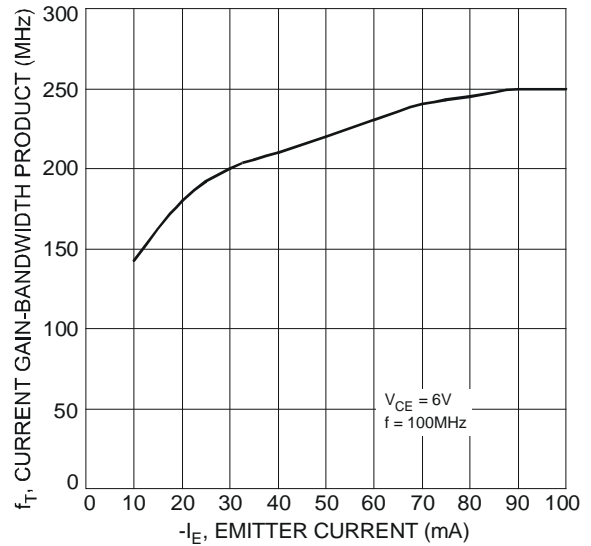


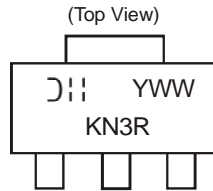
Fig. 8 Typical Gain-Bandwidth Product vs. Emitter Current

## Ordering Information (Note 5)

Device	Packaging	Shipping
2DD2098R-13	SOT89-3L	2500/Tape & Reel

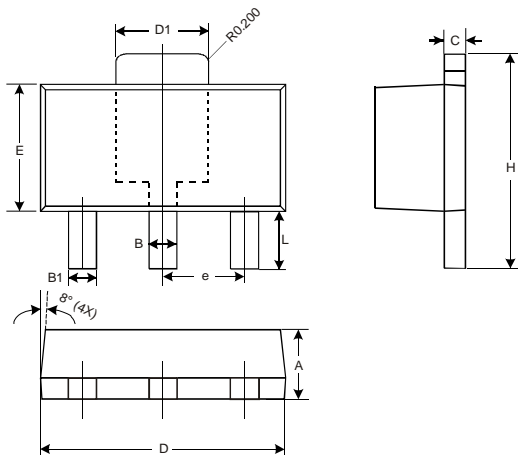
Notes: 5. For packaging details, please see below or go to our website at <http://www.diodes.com/ap02007.pdf>.

## Marking Information



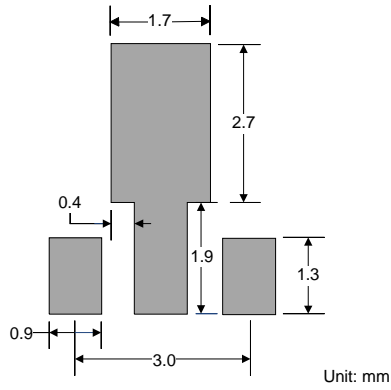
KN3R = Product Type Marking Code  
 DII = Manufacturer's Marking Code  
 YWW = Date Code Marking  
 Y = Last digit of year ex: 7 = 2007  
 WW = Week code 01 - 52

## Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

## Suggested Pad Layout



### IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

### LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9